

INCHANGE SEMICONDUCTOR

isc Silicon NPN Darlington Power Transistor

2SD1988

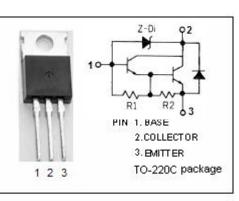
DESCRIPTION

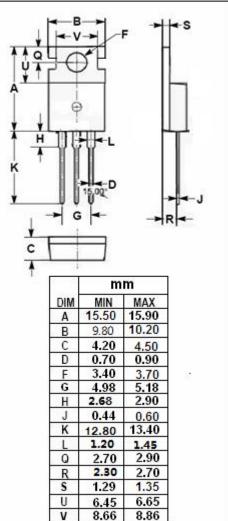
- · High DC Current Gain-
- : h_{FE} = 3000(Min)@ I_C= 1A
- Low Collector-Emitter Saturation Voltage-
- : V_{CE(sat)} = 1.5V(Max)@ I_C= 1A
- Incorporating a built-in zener diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- · Low-frequency amplifications.
- Power amplifier applications.

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	40-50	V	
V _{CEO}	Collector-Emitter Voltage	40-50	V	
V _{EBO}	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	2	A	
I _{CM}	Base Current-Peak	3	A	
Pc	Collector Power Dissipation @ T_c =25 °C	25	W	
TJ	Junction Temperature	150	°C	
T _{stg}	Storage Temperature Range	-55~150	°C	





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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; I _B = 0	40		50	V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C =0.1mA; I _E = 0	40		50	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1Α; I _B = 1mΑ			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1Α; I _B = 1mA			2.0	V
І _{сво}	Collector Cutoff Current	V _{CB} = 30V; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			3.0	mA
h _{FE}	DC Current Gain	Ic= 1A; Vce= 2V	3000			
f⊤	Current-Gain—Bandwidth Product	I _C = 100mA; V _{CE} = 5V		100		MHz

NOTICE:

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